INFORMATION DISCLOSURE STATEMENT

Applicant

Smith, et al.

App. No.

: Unknown

Filed

: Herewith

For

STRUCTURE AND METHOD OF

FABRICATING A TRANSISTOR

HAVING A TRENCH GATE

Examiner

Unknown

Group Art Unit

Unknown

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing 4 references that are also enclosed. This Information Disclosure Statement is being filed within three months of the filing date of this application and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated

Bv-

Karen J. Lenker

Registration No. 54,618 Customer No. 20,995 (949) 760-0404

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FORM	PTO-1449
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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE ATTY. DOCKET NO. MICRON.271A

APPLICATION NO. Unknown

INFORMATION DISCLOSURE STATEMENT

BY APPLICANT

APPLICANT Smith, et al.

(USE SEVERAL SHEETS IF NECESSARY)

GROUP FILING DATE Unknown Herewith

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
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FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	*						

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)					
	Yanagisawa, et al.; TRENCH TRANSISTOR CELL WITH SELF-ALIGNED CONTACT (TSAC) FOR MEGABIT MOS DRAM; 1st LSI Division, NEC Corporation; 1120 Shimokuzawa, Sagamihara, Kanagawa 229, Japan; Pages 132-135.					
	Landgraf, et al.; SCALABLE HIGH VOLTAGE TRENCHGATE TRANSISTOR FOR FLASH; University of Regensburg, Conference: ESSDERC 2000; 93040 Regensburg, Germany; Pages 380-383.					
	Hieda, et al.; SUB-HALF-MICROMETER CONCAVE MOSFET WITH DOUBLE LDD STRUCTURE; IEEE Transactions on Election Devices, Vol. 39, No. 3, March, 1992, Pages 671-676.					
	Sakao, et al. A STRAIGHT-LINE TRENCH ISOLATION AND TRENCH-GATE TRANSISTOR (SLIT) CELL FOR GIGA-BIT DRAMS; ULSI Device Development Laboratories, NEC Corporation; 1120, Shimokuzawa, Sagamihara, Kanagawa 229, Japan; Pages 19 and 20.					

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EXAMINER	7
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DATE CONSIDERED

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.